NSN 5962-01-303-8882

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View Online at https://aerobasegroup.com/nsn/5962-01-303-8882 **Overall Length:** 0.960 inches **Overall Height:** 0.400 inches Overall Width: 0.320 inches **Body Length:** 0.960 inches **Body Width:** 0.310 inches **Body Height:** 0.185 inches **Maximum Power Dissipation Rating:** 794.0 milliwatts **Operating Tempurature Range:** -55.0/+125.0 degrees celsius **Storage Tempurature Range:** -65.0/+150.0 degrees celsius **Features Provided:** Burn in and bipolar and hermetically sealed and programmable and 3-state output **Inclosure Material:** Ceramic **Inclosure Configuration:** Dual-in-line **Output Logic Form:** Transistor-transistor logic

Input Circuit Pattern:

12 input

Case Outline Source And Designator:

D-6 mil-m-38510

Terminal Surface Treatment:

Voltage Rating And Type Per Characteristic:

-0.5 volts power source and 7.0 volts power source

Time Rating Per Chacteristic:

85.00 nanoseconds propagation delay time, low to high level output and 85.00 nanoseconds propagation delay time, high to low level output

Memory Device Type:

Prom

Memory Capacity:

Unknown

Test Data Document:

96906-mil-std-883 standard (includes industry or association standards, individual manufactureer standards, etc.).

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Terminal Type Ar	nd Quantity:
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18 printed circuit

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

Fiig:

A458a0